

November 1997 - Revised May 2000

High Speed CMOS Logic Quad Buffer, Three-State

Features

- Three-State Outputs
- Separate Output Enable Inputs
- Fanout (Over Temperature Range)
 - Standard Outputs 10 LSTTL Loads
 - Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range . . . -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
 - 2V to 6V Operation
 - High Noise Immunity: $N_{IL} = 30\%$, $N_{IH} = 30\%$ of V_{CC} at $V_{CC} = 5V$
- HCT Types
 - 4.5V to 5.5V Operation
 - Direct LSTTL Input Logic Compatibility, $V_{IL} = 0.8V$ (Max), $V_{IH} = 2V$ (Min)
 - CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL} , V_{OH}

Description

The 'HC125 and 'HCT125 contain 4 independent three-state buffers, each having its own output enable input, which when "HIGH" puts the output in the high impedance state.

Ordering Information

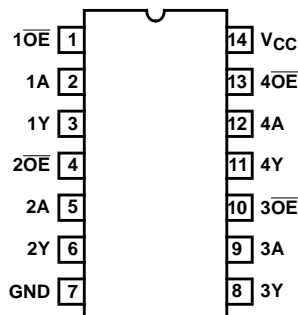
PART NUMBER	TEMP. RANGE (°C)	PACKAGE
CD54HC125F	-55 to 125	14 Ld CERDIP
CD54HC125F3A	-55 to 125	14 Ld CERDIP
CD74HC125E	-55 to 125	14 Ld PDIP
CD74HC125M	-55 to 125	14 Ld SOIC
CD54HCT125F3A	-55 to 125	14 Ld CERDIP
CD74HCT125E	-55 to 125	14 Ld PDIP
CD74HCT125M	-55 to 125	14 Ld SOIC

NOTES:

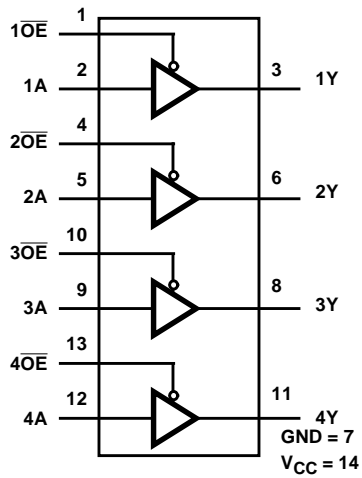
1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
2. Wafer and die for this part number is available which meets all electrical specifications. Please contact your local TI sales office or customer service for ordering information.

Pinout

CD54HC125, CD54HCT125
(CERDIP)
CD74HC125, CD74HCT125
(PDIP, SOIC)
TOP VIEW



Functional Diagram



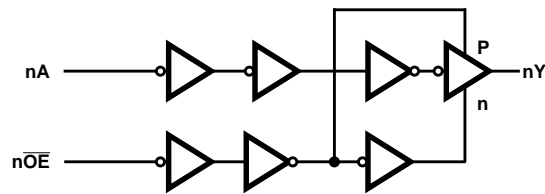
TRUTH TABLE

INPUTS		OUTPUTS
nA	nOE	nY
H	L	H
L	L	L
X	H	Z

NOTE:

- H = High Voltage Level
- L = Low Voltage Level
- X = Don't Care
- Z = High Impedance, OFF State

Logic Diagram



CD54/74HC125, CD54/74HCT125

Absolute Maximum Ratings

DC Supply Voltage, V_{CC}	-0.5V to 7V
DC Input Diode Current, I_{IK}	
For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$	$\pm 20mA$
DC Output Diode Current, I_{OK}	
For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$	$\pm 20mA$
DC Drain Current, per Output, I_O	
For $-0.5V < V_O < V_{CC} + 0.5V$	$\pm 35mA$
DC Output Source or Sink Current per Output Pin, I_O	
For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$	$\pm 25mA$
DC V_{CC} or Ground Current, I_{CC}	$\pm 70mA$

Thermal Information

Thermal Resistance (Typical, Note 3)	θ_{JA} (°C/W)
PDIP Package	90
SOIC Package	175
Maximum Junction Temperature	150°C
Maximum Storage Temperature Range	-65°C to 150°C
Maximum Lead Temperature (Soldering 10s)	300°C
(SOIC - Lead Tips Only)	

Operating Conditions

Temperature Range (T_A)	-55°C to 125°C
Supply Voltage Range, V_{CC}	
HC Types2V to 6V
HCT Types	4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O	0V to V_{CC}
Input Rise and Fall Time	
2V	1000ns (Max)
4.5V	500ns (Max)
6V	400ns (Max)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

- θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads	V_{OH}	V_{IH} or V_{IL}	-6	4.5	3.98	-	-	3.84	-	3.7	-	V
			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads	V_{OL}	V_{IH} or V_{IL}	6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	± 0.1	-	± 1	-	± 1	μA

CD54/74HC125, CD54/74HCT125

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V _{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V _I (V)	I _O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Quiescent Device Current	I _{CC}	V _{CC} or GND	0	6	-	-	8	-	80	-	160	μA
Three-State Leakage Current	I _{OZ}	V _{IL} or V _{IH}	-	6	-	-	±0.5	-	±5	-	±10	μA
HCT TYPES												
High Level Input Voltage	V _{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V _{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V _{OH}	V _{IH} or V _{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V _{OL}	V _{IH} or V _{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I _I	V _{CC} to GND	0	5.5	-	-	±0.1	-	±1	-	±1	μA
Quiescent Device Current	I _{CC}	V _{CC} or GND	0	5.5	-	-	8	-	80	-	160	μA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load (Note 4)	ΔI _{CC}	V _{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μA
Three-State Leakage Current	I _{OZ}	V _{IL} or V _{IH}	-	5.5	-	-	±0.5	-	±5	-	±10	μA

NOTE:

- For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
nA, nOE	1

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g., 360μA max at 25°C.

CD54/74HC125, CD54/74HCT125

Switching Specifications Input $t_r, t_f = 6\text{ns}$

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C		-40°C TO 85°C	-55°C TO 125°C	UNITS
				TYP	MAX	MAX	MAX	
HC TYPES								
Propagation Delay Time nA to nY	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	2	-	100	125	150	ns
			4.5	-	20	25	30	ns
		$C_L = 15\text{pF}$	5	8	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	17	21	26	ns
Enable Delay Time	t_{PZL}, t_{PZH}	$C_L = 50\text{pF}$	2	-	125	155	190	ns
			4.5	-	25	31	38	ns
		$C_L = 15\text{pF}$	5	10	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	21	26	32	ns
Disable Delay Time	t_{PLZ}, t_{PHZ}	$C_L = 50\text{pF}$	2	-	125	155	190	ns
		$C_L = 50\text{pF}$	4.5	-	25	31	38	ns
		$C_L = 15\text{pF}$	5	10	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	21	26	32	ns
Output Transition Time	t_{TLH}, t_{THL}	$C_L = 50\text{pF}$	2	-	60	75	90	ns
			4.5	-	12	15	18	ns
			6	-	10	13	15	ns
Input Capacitance	C_I	-	-	-	10	10	10	pF
Three-State Output Capacitance	C_O	-	-	-	20	20	20	pF
Power Dissipation Capacitance (Notes 5, 6)	C_{PD}	-	5	29	-	-	-	pF
HCT TYPES								
Propagation Delay Time nA to nY	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	4.5	-	25	31	38	ns
		$C_L = 15\text{pF}$	5	10	-	-	-	ns
Output Enable Time	t_{PZL}, t_{PZH}	$C_L = 50\text{pF}$	4.5	-	25	31	38	ns
		$C_L = 15\text{pF}$	5	10	-	-	-	ns
Output Disabling Time	t_{PLZ}, t_{PHZ}	$C_L = 50\text{pF}$	4.5	-	28	35	42	ns
		$C_L = 15\text{pF}$	5	11	-	-	-	ns
Output Transition Times	t_{TLH}, t_{THL}	$C_L = 50\text{pF}$	4.5	-	12	15	18	ns
Input Capacitance	C_I	-	-	-	10	10	10	pF
Three-State Output Capacitance	C_O	-	-	-	20	20	20	pF
Power Dissipation Capacitance (Notes 5, 6)	C_{PD}	-	5	34	-	-	-	pF

NOTES:

5. C_{PD} is used to determine the dynamic power consumption, per channel.
6. $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = Input Frequency, f_O = Output Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms



FIGURE 1. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC



FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

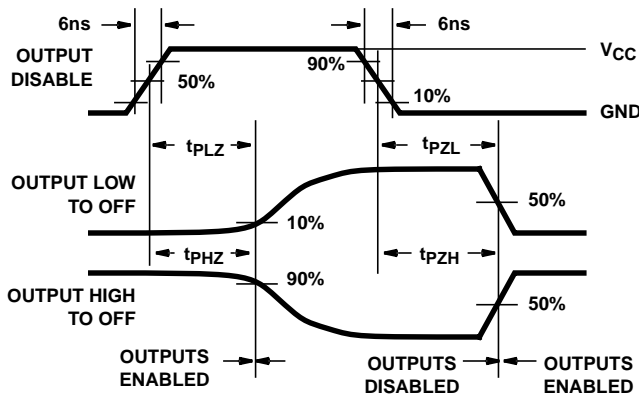


FIGURE 3. HC THREE-STATE PROPAGATION DELAY WAVEFORM

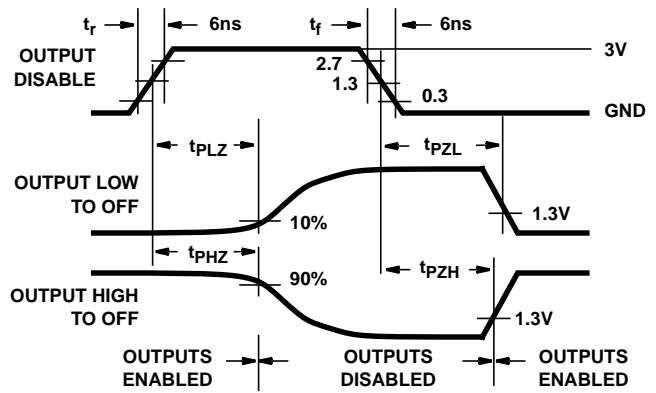
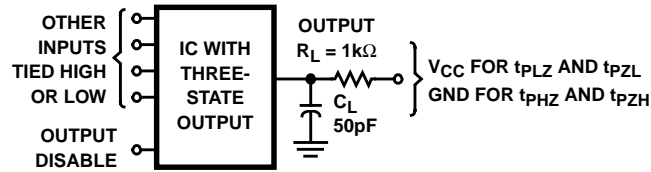


FIGURE 4. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output $R_L = 1k\Omega$ V_{CC} , $C_L = 50pF$.

FIGURE 5. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT

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